

Linear Systems Log Conformance Monolithic Dual NPN

The LS3250A is a monolithic pair of NPN transistors mounted in a single P-DIP package. The monolithic dual chip design reduces parasitics and is ideal for use in tracking applications.

The 8 Pin P-DIP provides ease of manufacturing, and the symmetrical pinout prevents improper orientation.

(See Packaging Information).

LS3250A Features:

- Tight matching
- Low Output Capacitance

FEATURES

TIGHT MATCHING	≤ 2mV
THERMAL TRACKING	≤ 3μV/°C
ABSOLUTE MAXIMUM RATINGS ¹ @ 25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-65°C to +150°C
Operating Junction Temperature	-55°C to +150°C
Maximum Power Dissipation	
Continuous Power Dissipation	TBD
Maximum Currents	
Collector Current	50mA
Maximum Voltages	
Collector to Collector Voltage	80V

MATCHING CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$ V_{BE1} - V_{BE2} $	Base Emitter Voltage Differential	--	--	2	mV	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$
$\Delta V_{BE1} - V_{BE2} / \Delta T$	Base Emitter Voltage Differential Change with Temperature	--	-	3	μV/°C	$I_C = 10\text{μA}, V_{CE} = 5\text{V}$ $T_A = -40\text{°C to } +85\text{°C}$
$ I_{B1} - I_{B2} $	Base Current Differential	--	--	10	nA	$I_C = 10\text{μA}, V_{CE} = 5\text{V}$
$ \Delta (I_{B1} - I_{B2}) / \Delta T$	Base Current Differential Change with Temperature	--	--	0.5	nA/°C	$I_C = 10\text{μA}, V_{CE} = 5\text{V}$ $T_A = -40\text{°C to } +85\text{°C}$
h_{FE1} / h_{FE2}	DC Current Gain Differential	--	--	10	%	$I_C = 10\text{μA}, V_{CE} = 5\text{V}$

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
V_{CBO}	Collector to Base Voltage	45	--	--	V	$I_C = 10\text{mA}, I_E = 0$
V_{CEO}	Collector to Emitter Voltage	45	--	--	V	$I_C = 10\text{μA}, I_B = 0$
V_{EBO} ²	Emitter-Base Breakdown Voltage	6.2	--	--	V	$I_E = 10\text{μA}, I_C = 0$
V_{CCO}	Collector to Collector Voltage	80	--	--	V	$I_C = 10\text{μA}, I_E = 0$
h_{FE}	DC Current Gain	150	--	--		$I_C = 10\text{μA}, V_{CE} = 5\text{V}$
		120	--	--		$I_C = 100\text{μA}, V_{CE} = 5\text{V}$
		100	--	--		$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
$V_{CE(SAT)}$	Collector Saturation Voltage	--	--	0.25	V	$I_C = 100\text{mA}, I_B = 10\text{mA}$
I_{EBO}	Emitter Cutoff Current	--	--	0.2	nA	$I_C = 0\text{A}, V_{CB} = 3\text{V}$
I_{CBO}	Collector Cutoff Current	--	--	0.2	nA	$I_E = 0\text{A}, V_{CB} = 20\text{V}$
C_{OBO}	Output Capacitance	--	--	2	pF	$I_E = 0\text{A}, V_{CB} = 10\text{V}$
I_{C1C2}	Collector to Collector Leakage Current	--	--	1	nA	$V_{CC} = \pm 80\text{V}$
f_T	Current Gain Bandwidth Product	--	--	600	MHz	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
NF	Narrow Band Noise Figure	--	--	3	dB	$I_C = 100\text{μA}, V_{CE} = 5\text{V}, BW = 200\text{Hz}, R_B = 10\Omega, f = 1\text{KHz}$

Notes:

1. Absolute Maximum ratings are limiting values above which serviceability may be impaired
2. The reverse base-to-emitter voltage must never exceed 6.2 volts; the reverse base-to-emitter current must never exceed 10μA.



Available Packages:

LS3250A in P-DIP
LS3250A available as bare die

Please contact Micross for full package and die dimensions:

Email: chipcomponents@micross.com
Web: www.micross.com/distribution.aspx

P-DIP (Top View)

